



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

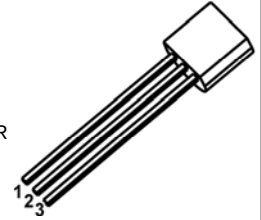
B772S TRANSISTOR (PNP)

FEATURES

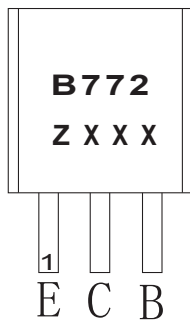
- Low speed switching

TO-92

1. EMITTER
2. COLLECTOR
3. BASE

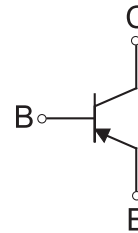


MARKING



B772=Device code
Z=Rank of h_{FE}
XXX=Code
GXX=Green molding compound device
CXX=Normal molding compound device

Equivalent Circuit



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
B772S	TO-92	Bulk	1000pcs/Bag
B772S-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	0.625	W
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	200	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS

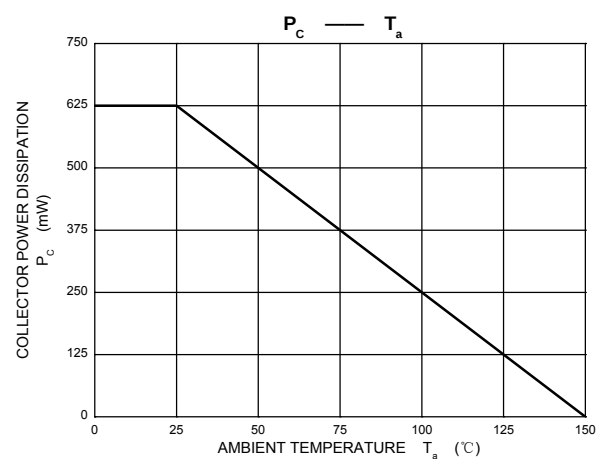
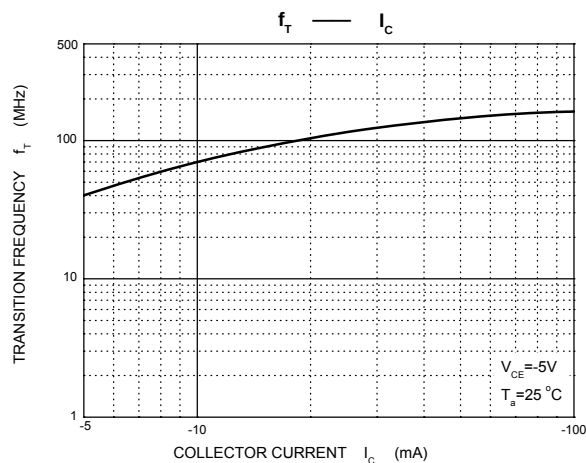
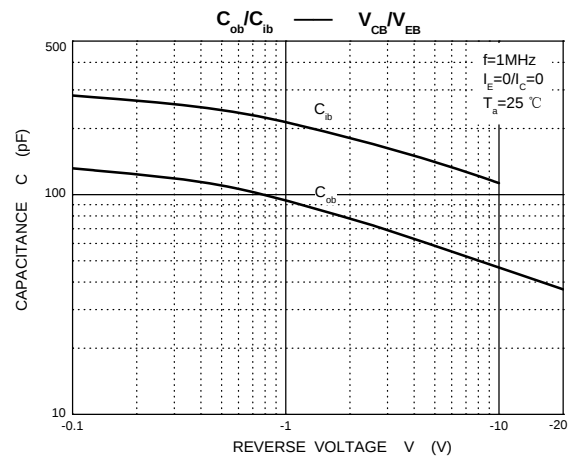
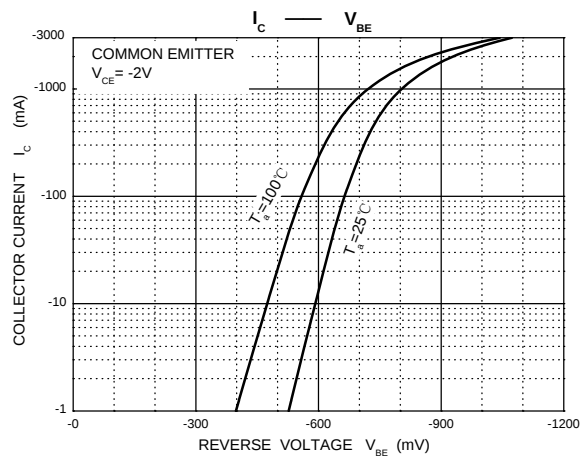
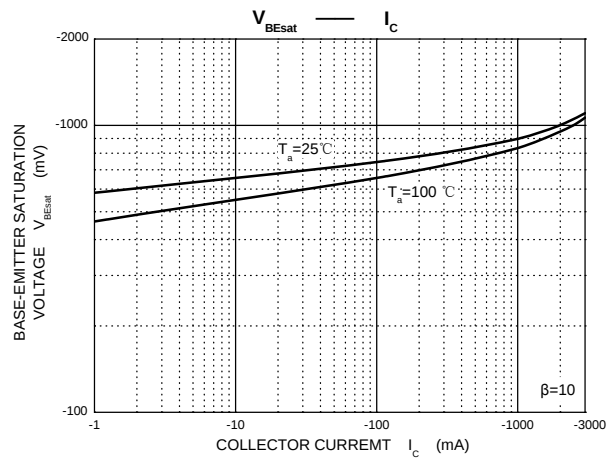
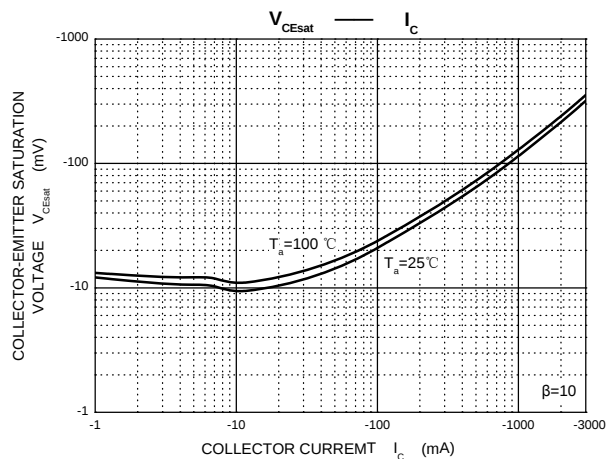
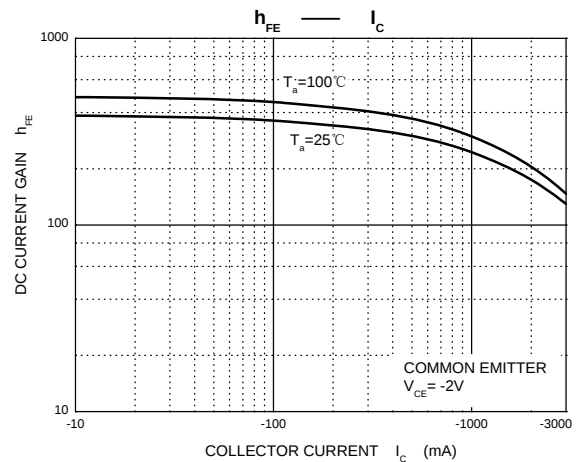
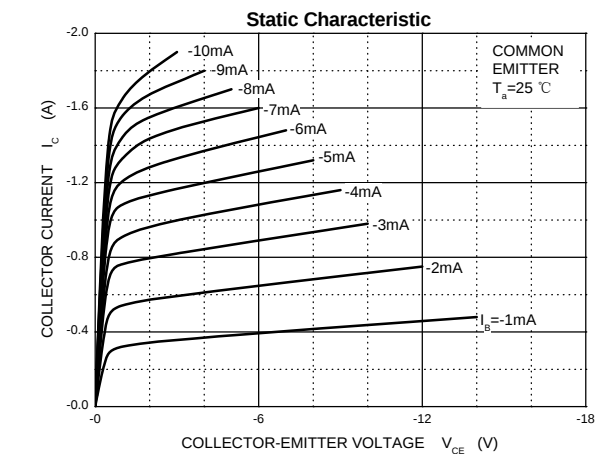
$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E = 0$			-1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -30\text{V}, I_B = 0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6\text{V}, I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -1\text{A}$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -0.2\text{A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{A}, I_B = -0.2\text{A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -0.1\text{A}$ $f = 10\text{MHz}$	50	80		MHz

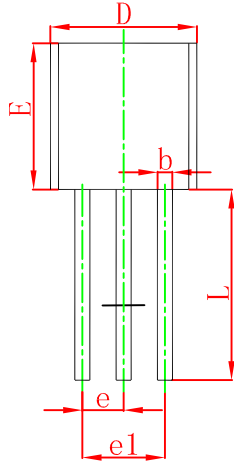
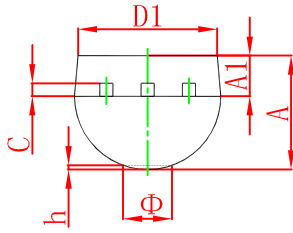
CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Typical Characteristics

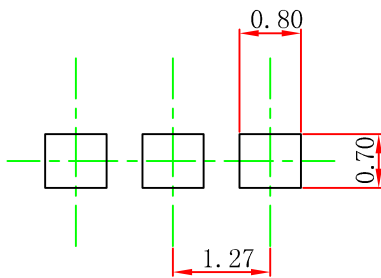


TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout



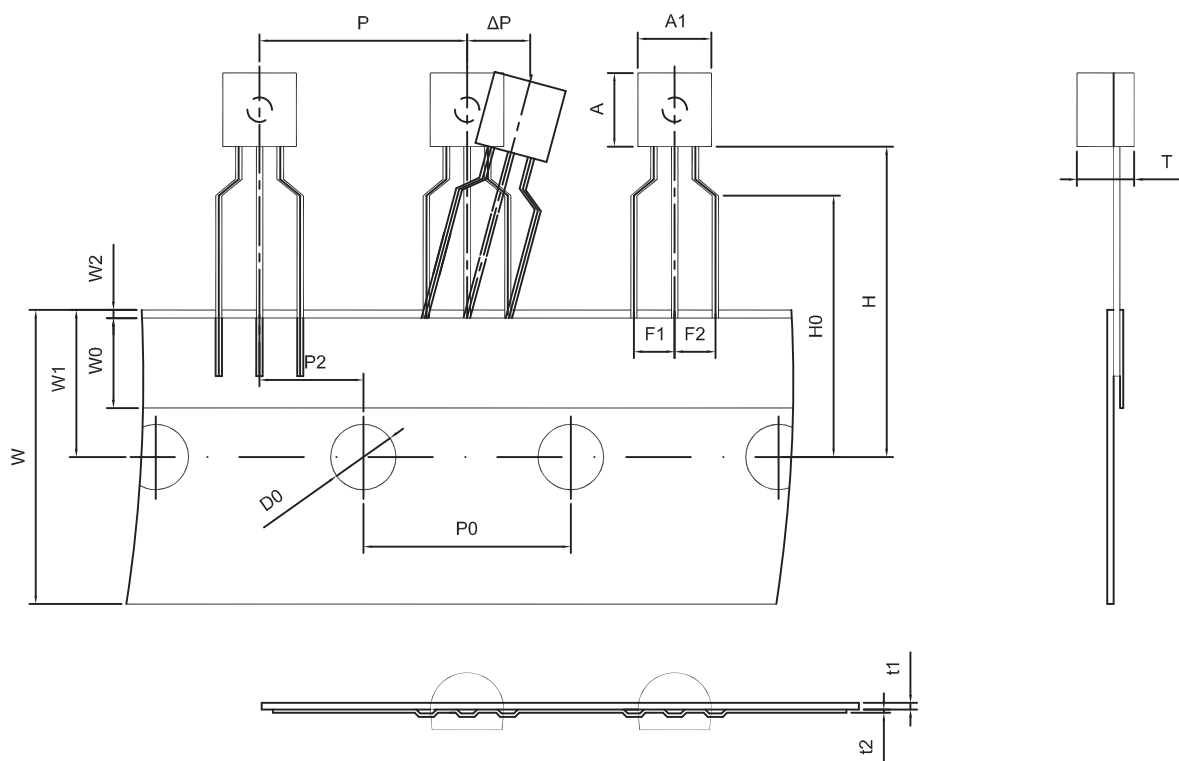
Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

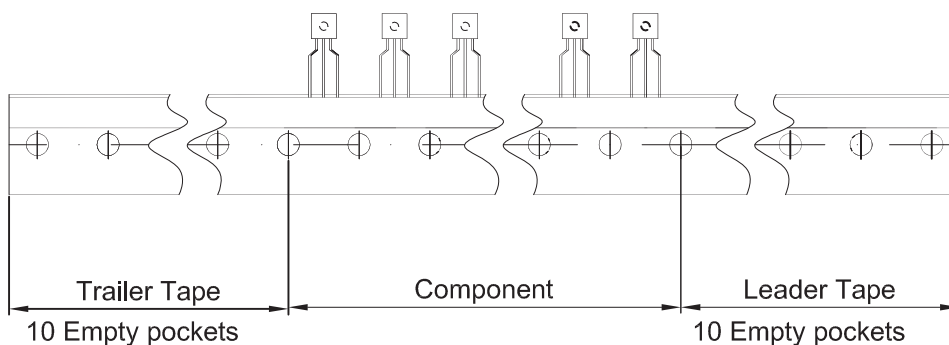
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TO-92 PACKAGE TAPING DIMENSION



Dimiensions are in millimeter

A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250